

### AMENDMENTS TO THE SPECIFICATION

#### In the Specification:

Please amend the paragraph at page 2, lines 3-11 as follows:

The process of manufacturing semiconductors (*e.g.*, integrated circuits, ICs, chips) employing masks typically consists of more than a hundred steps, during which hundreds of copies of an integrated circuit may be formed on a single wafer. Generally, the process involves creating several patterned layers on and into the substrate that ultimately forms the complete integrated circuit. The patterned layers are created, in part, by the light that passes through the masks. A series of lenses provides for reduction in size ~~form~~ from the mask to the projected image onto the resist. The optical equipment for traditional photolithographic processes requires significant capital investment.

Please amend the paragraph at page 2, lines 22-32 as follows:

In a conventional nanoprint process a UV-transmittable quartz mask/mold is pressed into a thin film of low viscosity UV-curable monomer coated onto a substrate. Subsequent exposure of the substrate by UV-irradiation through the mask/mold results in polymerization and curing of the resist in the imprinted area. Thereafter the mold is removed leaving an inverted three-dimensional replica of its pattern into the cured imprint polymer. Finally, the residual imprint layer in the depressed areas is removed by high anisotropic reactive ion etching. One advantage is that the circuit designers do not need to be concerned about optical proximity correction which otherwise limits how patterns are ~~placed~~ placed on the mask. Furthermore, patterning on top of a grating or other surfaces with severe topological features is possible providing significant advantages in MEMS applications.

Please amend the paragraph at page 5, lines 8-9 as follows:

Fig. 7 is an illustration of a substrate subjected to exposure ~~though~~ through a mask which has been produced in accordance with an aspect of the present invention.

Please amend the Abstract as shown below:

A mask is provided to be used with nanoprnt lithography processes to facilitate [[the]] reproduction of small features required for the production of integrated circuits. A translucent substrate is provided along with one or more three-dimensional features that include one or more vertical sidewalls. An absorbing material is deposited upon one or more of the vertical sidewalls so that light in an incident direction to an upper surface of the substrate will be absorbed by the absorbing material, resulting in light blocking features. One or more horizontal surfaces are formed upon one or more of the three-dimensional features, ~~that~~ which allow light rays to exit a lower surface of the substrate unobstructed by the absorbing material.